

POSTER TITLE	AUTHOR(S)	COMPANY
An Analysis of EUV Technology Cost-of-Ownership	W. Trybula, P. Seidel	<i>ISMT</i>
Stand-Alone At-Wavelength Mask Inspection Microscope (MIM) for EUV Mask Defect Inspection Using a Laser Plasma Source	R.C.C. Perera	<i>EUV Technology</i>
High Speed EUV-Reflectometer with Compact Discharge EUV Source Designed for Mask-Blank Inspection	R. Lebert ¹ , L. Juschkin ¹ , M. Meisen ¹ , A. Nazareko ¹ , M.C. Schurmann ² , T. Misalla ² , L. Aschke ³ , H. Sauerbrei ³ , M. Schiffler ³ , G. Ulm ⁴ , R.M. Klein ⁴ , F. Scholze ⁴	<i>¹AIXUV GmbH, ²JENOPTIK Mikrotechnik GmbH, ³Schott Lithotec AG, ⁴Physikalisch-Technische Bundesanstalt</i>
Influence of Multilayer Stress Distribution on EUV Mask in-Place Distortion	A. Chiba, M. Sugawara, H. Yamanashi, I. Nishiyama	<i>ASET</i>
Printability Analysis of Attenuated Phase-Shifting Mask Considering Exposure Bandwidth	M. Sugawara, A. Chiba, H. Oizumi, H. Yamanashi, I. Nishiyama	<i>ASET</i>
Visible Light Scattering from Defects in EUV Mask Blanks: 3-D Modeling	M. Ito, I. Nishiyama, S. Okazaki	<i>ASET</i>
Development of a Mask-Scan EB Mask Writing System	M. Ogasawara, S. Nishimura, K. Akeno, S. Mitsui, M. Shimizu, H. Kusakabe, T. Tojo	<i>ASET</i>
Evaluation of Finished EUV Lithography Mask Using a Mirau Interferometric Microscope	H. Kinoshita ¹ , T. Haga ² , K. Hamamoto ¹ , S. Takada ¹ , N. Kazui ¹ , S. Kakunai ¹ , H. Tsubakino ¹ , T. Watanabe ¹	<i>¹Himeji Institute, ²NJT Telecommunications Energy Laboratories</i>

POSTER TITLE	AUTHOR(S)	COMPANY
Correlation of Absorber Films Properties with Patterned Film Characteristics on Square Format EUV Lithography Masks	K. Racette, E. Fisch, C. Huang, M. Lawliss, C. Williams	<i>IBM Microelectronics</i>
Requirements for Fabricating Attenuated Phase Shift Masks for EUV Lithography	S.-I Han, S.D. Hector, G. Edwards, P.J.S. Mangat	<i>Motorola DigitalDNA™ Labs</i>
Improved Characteristics of ULE® Glass for Meeting EUV Lithography Needs	B. Ackerman, C. Heckle, K. Hrdina, J. Maxon, B. McLean, D. Navan, M. Wasilewski	<i>Corning, Inc.</i>
EUV Mask Blank Substrates	J. Teisson, D. Bardon, S. Chaillot	<i>SAGEM SA</i>
The European Mask Blank, Mask, & Metrology Program: EXTUMASK	J. Rau ¹ , A. Ehrmann ¹ , F.-M. Kamm ¹ , J. Mathuni ¹ , K. Vaas ¹ , A. Wolter ¹ , F. Letzkus ² , R. Springer ² , L. Aschke ³ , H. Becker ³ , G. Hess ³ , S. Kirchner ³ , T. Leutbecher ³ , N. Olschewski ³ , H. Sauerbrei ³ , M. Schiffler ³ , K. Walter ³ , E. Quesnel ⁴ , J. Hue ⁴ , J.-Y Robic ⁴ , C. Vannuffel ⁴ , P. Schiavone ⁵	<i>¹Infineon Technologies AG, ²Institut für Mikroelektronik Stuttgart, ³Schott Lithotec AG, ⁴CEA/Leti, ⁵CNRS/LTM</i>
Mo/Si Multilayers for EUV Lithography Masks by Ion Beam Sputter Deposition	T. Chasse ¹ , H. Neumann ¹ , W. Frank ¹ , F. Frost ¹ , D. Hirsch ¹ , A. Schindler ¹ , G. Wagner ² , M. Lorenz ² , B. Ocker ³ , B. Rauschenbach ¹	<i>¹Institute for Surface Modification, ²Universität Leipzig, ³Singulus Technologies AG</i>
EUV Lithography Multilayer Stress Measurement Analysis	Z. Feng ¹ , A. Mikkelson ¹ , P. Reu ¹ , R. Engelstad ¹ , E. Lovell ¹ , K. Blaedel ² , A. Claudet ²	<i>¹University of Wisconsin, ²Lawrence Livermore National Laboratory</i>

POSTER TITLE	AUTHOR(S)	COMPANY
EUV Lithography Mask Flatness & Electrostatic Chucking Analysis	A. Mikkelsen ¹ , R. Engelstad ¹ , E. Lovell ¹ , K. Blaedel ² , A. Claudet ²	¹ University of Wisconsin, ² Lawrence Livermore National Laboratory
Purification of Photolithography Purge Gases: Quantitative Analysis & Removal of Hydrocarbons & Sulfur Contaminants to Parts-per-Trillion Levels	A. Tram, J.J. Spiegelman, X. Jiang, D. Alvarez, Jr.	AERONEX)
Improvement of a Visible PDI System for Aspherical Mirror Measurement	K. Ota ¹ , M. Ishii ¹ , T. Yamamoto ² , Y. Fukuda ² , H. Ichikawa ² , Y. Ouchi ² , K. Otaki ² , T. Gemma ²	¹ ASET, ² Nikon Corporation
Metrology for EUV Lithography at NIST	C. Tarrío, S. Grantham, R. Vest, T. Lucatorto	NIST
Evaluation of Ion Beam Sputtered Mo/Si Multilayers for EUV Lithography	H. Yamanashi, M. Sugawara, A. Chiba, H. Oizumi, I. Nishiyama	ASET
Compact In-Line Laser Plasma Reflectometer for the Measurement and Uniformity of EUV Lithography Mask Blank Multilayer Coatings	R. Perera, J. Underwood	EUV Technology
Capping Layers for EUV Lithography Optics	S. Bajt ¹ , M. Malinowski ² , J. Alameda ¹ , S. Baker ¹ , M. Clift ² , J. Harper ¹ , L. Klebanoff ²	¹ Lawrence Livermore National Laboratory, ² Sandia National Laboratories
Increasing the Radiation Intensity for EUV Lithography	M. Briac ¹ , P. Choi ² , V. Braic ¹ , S. Zakharov ² , C. Dumitrescu ² , G. Pavelescu ¹ , M. Balaceunu ¹	¹ National Institute for Optoelectronics, Romania, ² EPPRA sas



TUESDAY & WEDNESDAY, October 15 & 16, 2002

Page 4

POSTER TITLE	AUTHOR(S)	COMPANY
Influence of the Multilayers on EUV Projection Optics	Y. Sekine ¹ , A. Suzuki ¹ , M. Hasegawa ¹ , S. Takeuchi ¹ , C. Ouchi ¹ , O. Kakuchi ¹ , Y. Watanabe ¹ , T. Hasegawa ¹ , S. Hara ¹ , K. Murakami ² , J. Saito ² , K. Ota ² , H. Kondo ² , M. Ishii ² , J. Kawakami ² , T. Oshino ² , K. Sugisaki ² , Y. Zhu ²	¹ Canon, Inc., ² Nikon Corporation
Effects of Processing Parameters on Line Edge Roughness (LER)	B. Rice, H. Cao, J. Roberts, M. Chandhok	Intel Corporation
Screening of Basic Resist Materials and PAGs for EUV Lithography	W.-D. Domke ¹ , O. Kirch ¹ , K. Kragler ¹ , L. Lowack ¹ , U. Scheunemann ²	¹ Infineon Technologies, ² BESSY GmbH
Resist Process Issues at EUV Related to the Glass Transition changes Accompanying Film Thickness Reduction	I. Raptis ¹ , D. Niakoula ¹ , E. Tegou ¹ , P. Argitis ¹ , E. Gogolides ¹ , A.C. Cefalas ² , E. Sarantopoulou ²	¹ Institute of Microelectronics, Greece, ² National Hellenic Research Foundation, Greece
Intel EUV Resist Development	J. Roberts, H. Cao, E. Panning, R. Meagley, M. Chandhok, J. Dalin, B. Rice	Intel Corporation
Shot Noise & Process Window Study for Printing Small Contacts Using EUV Lithography	S.H. Lee, J. Bjorkholm, R. Bristol, M. Chandhok	Intel Corporation
Silicon Photodiode Sensors for EUV Lithography Applications	R. Korde ¹ , C. Prince ¹ , D. Jovanovic ¹ , J. Seely ² , E. Gullikson ³	¹ International Radiation Detectors, ² Naval Research Laboratory, ³ Sandia National Laboratories

POSTER LISTING

POSTER TITLE	AUTHOR(S)	COMPANY
Compact Laboratory Sources: Calibration of EUV-2D Photoresist Simulation Parameters for Accurate Predictive Modeling	S. Robertson ¹ , P. Naulleau ² , D. O'Connell ³ , K. McDonald ³ , K. Goldberg ² , T. Delano ¹ , R. Brainard ¹	¹ Shibley Company, ² Lawrence Berkeley National Laboratory, ³ Sandia National Laboratories
"In-Band"-EUV Open Frame-Exposure System Based on a Compact Discharge EUV-Source	L. Juschkin ¹ , R. Lebert ¹ , U. Bieberle ¹ , M. Meisen ¹ , A. Nazareko ¹ , K. Kragler ¹ , W.-D. Domke ² , K. Lowack ²	¹ AIXUV GmbH, ² Infineon Technologies AG
The "EUV-Lamp": A Compact Source for EUV Technology	R. Lebert, L. Juschkin, B. Jagle	AIXUV GmbH
"In-House Beamlines" for Development of EUV Lithography Technology	R. Lebert ¹ , L. Juschkin ¹ , A. Nazareko ¹ , M.C. Schurmann ² , T. Misalla ² , L. Aschke ³ , K. Kragler ⁴	¹ AIXUV GmbH, ² JENOPTIK Mikrotechnik GmbH, ³ Schott Lithotec AG, ⁴ Infineon Technologies AG
Development of a Modular Laser-Plasma EUV Power Source for Micro-Lithography	B. Barthod ¹ , R. Bernard ¹ , E. Veran ¹ , J.M. Barbiche ² , E. Marquis ² , T. Ceccotti ³ , D. Descamps ³ , J.F. Hergott ³ , S. Hulin ³ , D. Normand ³ , M. Schmidt ³ , M. Segers ³ , O. Sublemontier ³ , P. Cormont ⁴ , M. Neu ⁴ , P.Y. Thro ⁴ , J.M. Weulersse ⁴	¹ Alcatel Vacuum Technology France, ² Thales Laser S.A., ³ Groupe d'Applications des Plasmas, ⁴ Laboratoire d'Applications des Lasers
A High Repetition Rate Discharge EUV Source	P. Choi ¹ , A. Conti ¹ , C. Dumitrescu ¹ , M. Favre ² , E. Wyndham ² , A. Yuan ¹ , S. Zakharov ¹	¹ EPPRA sas, ² Pontificia Universidad Catolica de Chile

POSTER TITLE	AUTHOR(S)	COMPANY
Performance Evaluation on Discharge EUV Sources Using 2-D Radiation MHD Simulation	S. Zakharov ¹ , P. Choi ¹ , V.G. Novikov ² , Y. Kroukovski ³	¹ EPPRA sas, ² Keldysh Institute of Applied Mathematics, Russia, ³ Institute of Mathematical Modeling Russia
Laser Plasma Radiation Source Based on a Laser-Irradiated Gas Puff Target for EUV Lithography Technologies	H. Fiedorowicz, A. Bartnik, R. Jarocki, J. Kostecki, J. Mikolajczyk, R. Rakowski, M. Szczurek	<i>Institute of Optoelectronics, Military Univ. of Technology, Poland</i>
Overview: Tools for EUV Lithography-Source Characterization & Optimization	M.C. Schurmann ¹ , T. Missalla ¹ , K. Mann ² , S. Kranzusch ² , R.M. Klein ³ , F. Scholze ³ , G. Ulm ³ , R. Lebert ⁴ , L. Juschkin ⁴	¹ JENOPTIK Mikrotechnik GmbH, ² Laser Laboratorium Gotteingen, ³ Physikalisch Technische Bundesanstalt, ⁴ AIXUV GmbH
Physics of Mass-Limited Laser-Plasma Sources for EUV Lithography	M.C. Richardson ¹ , C. Keyser ¹ , C.-S. Koay ¹ , I.C.E. Turcu ²	¹ Univ. of Central Florida, ² JMAR Research
High Efficiency EUV Radiation Source Generated by Laser-Produced-Plasma	I.C.E. Turcu ¹ , H. Rieger ¹ , J.H. Morris ¹ , M.F. Powers ¹ , A. Stone ¹ , J.H. Carosella ¹ , M.C. Richardson ² , C. Keyser ²	¹ JMAR Research, ² Univ. Of Central Florida
EUV Radiation from Fast Capillary Xenon Discharges	S. Katsuki ¹ , Y. Teramoto ² , T. Namihira ¹ , H. Akiyama ¹	¹ Kumamoto Univ., ² USHIO
High Power Lasers for Laser Produced Plasma (LPP) EUV Sources	S. Ellwi, A. Comley, M. Mason, D. Parsons-Karavassilis, I. Mercer, I. Henderson, M. Egan	<i>Powerlase Ltd.</i>

POSTER TITLE	AUTHOR(S)	COMPANY
Laser Heating of Nobel Gas Droplet Sprays: EUV Source Efficiency Considerations	H.M. Milchberg, J. Fan, S.J. McNaught, E. Parra	<i>Univ. of Maryland</i>
Compact Electron-Based EUV Source for Metrology	A. Egbert, B. Mader, B. Tkachenko, A. Ostendorf, B.N. Chichkov	<i>Laser Zentrum Hannover e.V.</i>
Recent Developments of CAPELLA, A Gas Discharge Source for EUV Lithography Approach	T. Gonthiez, E. Robert, O. Sarroukh, R. Viladrosa, C. Fleurier, J.M. Pouvesle, C. Cachoncinlle	<i>GREMI</i>
A Study of Cost-of-Ownership & Total System Balance in EUV Lithography	Y. Gomei	<i>Canon, Inc.</i>
BEL: Integration Progress	C. Vannuffel ¹ , J.-Y. Robic ¹ , C. Cachoncinlle ² , D. Bardon ³ , R. Geyl ³ , J.-F. Tanne ³ , B. Vidal ⁴ , S. Huelvan ⁵ , R. Marmoret ⁵ , T. Trublet ⁵	¹ CEA/LETI, ² GREMI, ³ SAGEM, ³ UDESAM, ⁴ CEA/DIF